



### 20V N-Channel Enhancement Mode MOSFET

Voltage

20 V

Current

500mA

#### **Features**

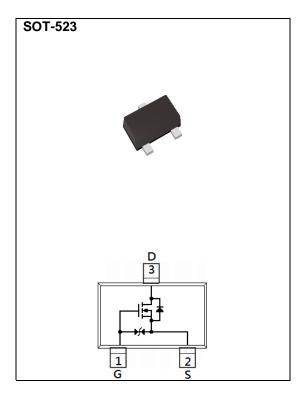
- Low Voltage Drive (1.2V).
- Advanced Trench Process Technology
- Specially Designed for Switch Load, PWM Application, etc.
- ESD Protected
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC61249 standard

#### **Mechanical Data**

• Case: SOT-523 Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.002 grams



### Maximum Ratings and Thermal Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

| PARAMETER  |                      | SYMBOL                           | LIMIT   | UNITS |  |
|--|----------------------|----------------------------------|---------|-------|--|
| Drain-Source Voltage   |                      | V <sub>DS</sub>                  | 20      | V     |  |
| Gate-Source Voltage  | V <sub>G</sub> s     | <u>+</u> 10                      |         |       |  |
| Continuous Drain Current(Note 4)                                       |                      | ID                               | 500     | mA    |  |
| Pulsed Drain Current <sup>(Note 1)</sup>                               |                      | I <sub>DM</sub>                  | 1000    |       |  |
| Power Dissipation  | T <sub>a</sub> =25°C | Po                               | 300     | mW    |  |
|  | Derate above 25°C    |                                  | 2.4     | mW/°C |  |
| Operating Junction and Storage Temperature Range                       |                      | T <sub>J</sub> ,T <sub>STG</sub> | -55~150 | °C    |  |
| Typical Thermal Resistance - Junction to Ambient <sup>(Note 3,4)</sup> |                      | ReJA                             | 417     | °C/W  |  |





## Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

| PARAMETER                        | SYMBOL              | TEST CONDITION  | MIN. | TYP. | MAX.        | UNITS |  |
|----------------------------------|---------------------|---|------|------|-------------|-------|--|
| Static                           |                     |   |      |      |             |       |  |
| Drain-Source Breakdown Voltage   | BV <sub>DSS</sub>   | V <sub>GS</sub> =0V, I <sub>D</sub> =250uA  | 20   | -    | -           |       |  |
| Gate Threshold Voltage           | $V_{GS(th)}$        | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA                                    | 0.3  | 0.64 | 0.9         | V     |  |
| Drain-Source On-State Resistance | R <sub>DS(on)</sub> | V <sub>GS</sub> =4.5V, I <sub>D</sub> =500mA  | -    | 310  | 400         | mΩ    |  |
|                                  |                     | V <sub>GS</sub> =2.5V, I <sub>D</sub> =200mA  | -    | 360  | 650         |       |  |
|                                  |                     | V <sub>GS</sub> =1.8V, I <sub>D</sub> =100mA  | -    | 430  | 800         |       |  |
|                                  |                     | V <sub>GS</sub> =1.5V, I <sub>D</sub> =50mA   | -    | 510  | 1200        |       |  |
|                                  |                     | V <sub>GS</sub> =1.2V, I <sub>D</sub> =20mA   | -    | 710  | 3000        |       |  |
| Zero Gate Voltage Drain Current  | I <sub>DSS</sub>    | V <sub>DS</sub> =16V, V <sub>GS</sub> =0V   | -    | -    | 1           | uA    |  |
| Gate-Source Leakage Current      | Igss                | V <sub>GS</sub> = <u>+</u> 8V, V <sub>DS</sub> =0V  | -    | -    | <u>+</u> 10 |       |  |
| Dynamic <sup>(Note 5)</sup>      |                     |   |      |      |             |       |  |
| Total Gate Charge                | $Q_g$               | V <sub>DS</sub> =10V, I <sub>D</sub> =500mA,<br>V <sub>GS</sub> =4.5V <sup>(Note 1,2)</sup> | -    | 1.4  | -           | nC    |  |
| Gate-Source Charge               | Qgs                 |   | -    | 0.22 | -           |       |  |
| Gate-Drain Charge                | $Q_{gd}$            |   | -    | 0.21 | -           |       |  |
| Input Capacitance                | Ciss                | V <sub>DS</sub> =10V, V <sub>GS</sub> =0V,<br>f=1MHZ  | -    | 67   | -           | pF    |  |
| Output Capacitance               | Coss                |   | -    | 19   | -           |       |  |
| Reverse Transfer Capacitance     | Crss                |   | -    | 6    | -           |       |  |
| Turn-On Delay Time               | td <sub>(on)</sub>  | $V_{DD}{=}10V,\ I_{D}{=}150mA,$ $V_{GS}{=}4.0V,$ $R_{G}{=}10\Omega^{(Note\ 1,2)}$           | -    | 2.8  | -           |       |  |
| Turn-On Rise Time                | tr                  |   | -    | 20   | -           | ns    |  |
| Turn-Off Delay Time              | td <sub>(off)</sub> |   | -    | 23   | -           |       |  |
| Turn-Off Fall Time               | tf                  |   | -    | 23   | -           |       |  |
| Drain-Source Diode               |                     |   |      |      |             |       |  |
| Maximum Continuous Drain-Source  |                     | ls  |      |      | 500         | m Λ   |  |
| Diode Forward Current            | IS                  |   | -    | -    | 500         | mA    |  |
| Diode Forward Voltage            | V <sub>SD</sub>     | I <sub>S</sub> =500mA, V <sub>GS</sub> =0V  | -    | 0.87 | 1.3         | V     |  |

#### NOTES:

- 1. Pulse width<300us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
- 4. The maximum current rating is package limited.
- 5. Guaranteed by design, not subject to production testing.





#### **TYPICAL CHARACTERISTIC CURVES**

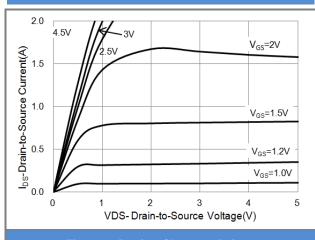


Fig.1 On-Region Characteristics

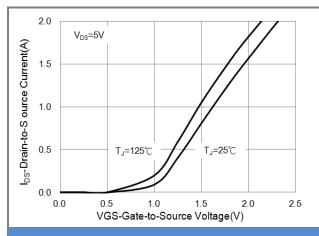


Fig.2 Transfer Characteristics

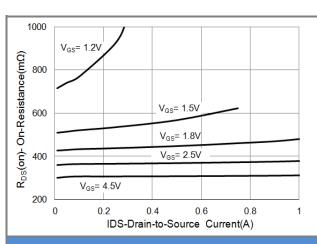


Fig.3 On-Resistance vs. Drain Current

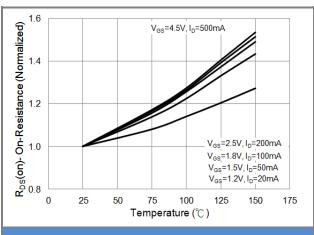
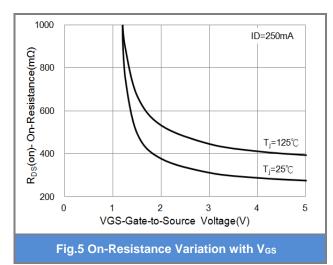
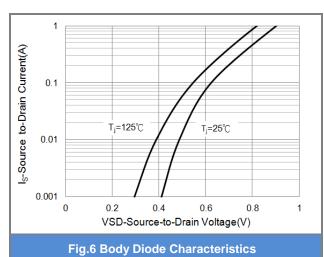


Fig.4 On-Resistance vs. Junction temperature









### **TYPICAL CHARACTERISTIC CURVES**

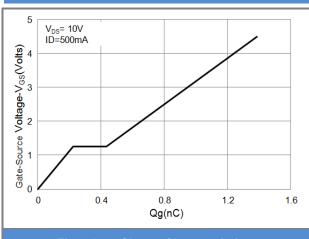


Fig.7 Gate-Charge Characteristics

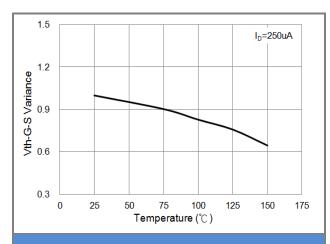


Fig.8 Threshold Voltage Variation with Temperature

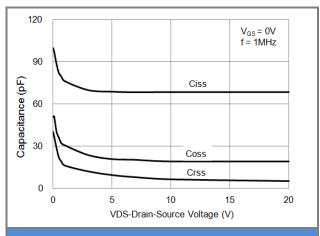


Fig.9 Capacitance vs. Drain-Source Voltage

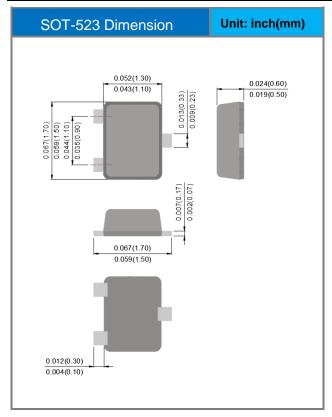


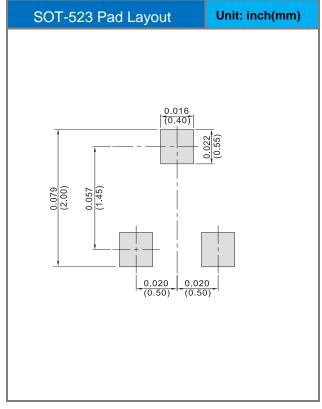


## Part No. Packing Code Version

| Part No. Packing Code | Package Type | Packing Type     | Marking | Version                        |
|-----------------------|--------------|------------------|---------|--------------------------------|
| PJE8408-AU_R1_000A1   | SOT-523      | 4K pcs / 7" reel | E08     | Halogen free<br>RoHS compliant |

## **Packaging Information & Mounting Pad Layout**









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